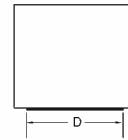
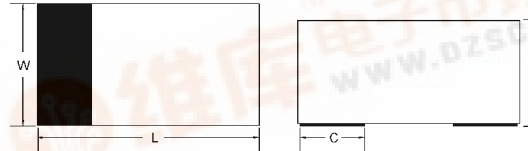




TSS42L/TSS43L

0.2Amp Surface Mount Schottky Barrier Diode

1005



Features

- ◇ Designed for mounting on small surface
- ◇ Extremely thin/leadless package
- ◇ Low capacitance
- ◇ Low forward voltage drop
- ◇ High temperature soldering:
260°C/10 seconds at terminals
- ◇ Chip version in 1005

Mechanical Data

- ◇ Case: 1005 Standard package, molded plastic
- ◇ Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- ◇ Polarity: Indicated by cathode band
- ◇ Mounting position: Any
- ◇ Package code: RW
- ◇ Weight: 0.006 gram (approximately)

ITEM	1005
L	0.102(2.60)
	0.095(2.40)
W	0.051(1.30)
	0.043(1.10)
T	0.035(0.90)
	0.027(0.70)
C	0.020(0.50)
D	Typical
	0.040(1.00)
	Typical

Dimensions in inches and (millimeters)

Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise specified

Type Number	Symbol	1005	Units
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Reverse Voltage	V_R	30	V
RMS Reverse Voltage	$V_{R(RMS)}$	21	V
Average Forward Current	I_O	200	mA
Repetitive Peak Forward Current	I_{FRM}	0.5	A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}	400	mA
Power Dissipation	P_d	200	mW
Forward Voltage	V_F	TSS42L/43L IF=200mA	1.0
		TSS42L IF=10mA	0.4
		TSS42L IF=50mA	0.65
		TSS43L IF=2mA	0.33
		TSS43L IF=15mA	0.45
Reverse Leakage Current $V_R=25V$	I_R	0.5	uA
Typical capacitance between terminals $V_R=1V, f=1.0MHz$ reverse voltage	C_J	10	pF
Reverse Recovery Time ($I_F=I_R=10mA, I_{rr}=0.1 \times I_R, R_L=100\Omega$)	T_{rr}	5	nS
Junction Temperature	T_J	-55 to + 125	°C
Storage Temperature	T_{STG}	-55 to + 125	°C

RATINGS AND CHARACTERISTIC CURVES(TSS42L/TSS43L)

Fig. 1 - Forward characteristics

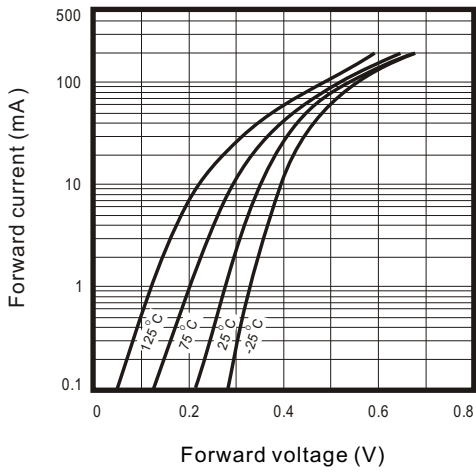


Fig. 2 - Reverse characteristics

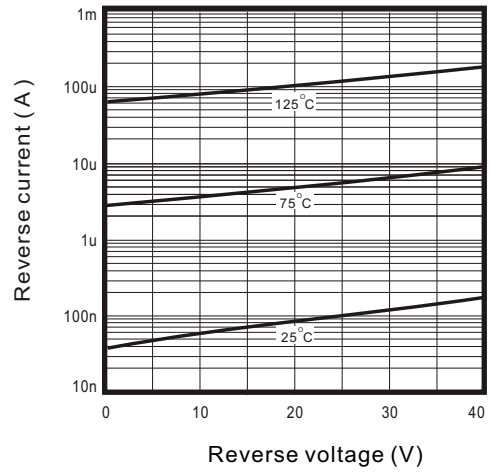


Fig.3 - Capacitance between terminals characteristics

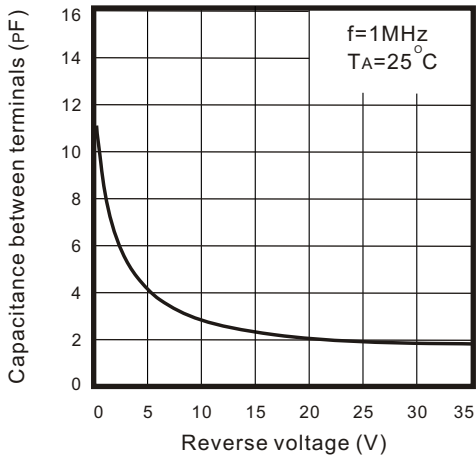


Fig.4 - Current derating curve

